

PRODUCT CHARACTERISTICS

V_{DSS}	650V
$R_{DS(ON)}$ Typ(@ $V_{GS}=10V$)	1.1 Ω
Q_g @typ	24.5nC
I_D	8A

APPLICATIONS

- * High efficiency switch mode power supplies
- * Electronic lamp ballasts based on half bridge
- * LED power supplies

FEATURE

- * High Switching Speed
- * Improved dv/dt capability

ORDER INFORMATION

Order Codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT8N65MC	TO-251	70 pieces/Tube

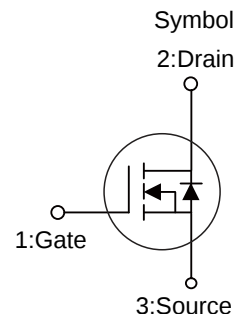
ABSOLUTE MAXIMUM RATINGS($T_A=25^{\circ}C$, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DSS}	650	V
Gate-Source Voltage	V_{GSS}	± 30	V
Drain Current Continuous(@ $V_{GS}=10V$, $T_A=25^{\circ}C$)	I_D	8	A
Drain Current Pulsed	I_{DM}	32	A
Avalanche Energy *	E_{AS}	845	mJ
Peak Diode Recovery dv/dt	dv/dt	5.0	V/ns
Power Dissipation	P_D	120	W
Junction Temperature	T_J	+150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$

THERMAL CHARACTERISTICS

Parameter	Symbol	Typ	Unit
Junction to Ambient	R_{thJA}	100	$^{\circ}C/W$
Junction to Case	R_{thJC}	1.04	$^{\circ}C/W$

Note: * EAS condition: $T_J=25^{\circ}C$, $V_{DD}=50V$, $V_G=10V$, $L=10mH$, $R_g=25\Omega$



TO-251



■ ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Off characteristics						
Drain to Source Breakdown Voltage	V _{DSS}	V _{GS} =0V, I _D =250μA	650	-	-	V
Drain to Source Leakage Current	I _{DSS}	V _{DS} =650V, V _{GS} =0V	-	-	1	μA
Gate to Source Forward Leakage	I _{GSS(F)}	V _{DS} =0V, V _{GS} =+30V	-	-	100	nA
Gate to Source Reverse Leakage	I _{GSS(R)}	V _{DS} =0V, V _{GS} =-30V	-	-	-100	nA
On characteristics						
Drain to Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =4A	-	1.1	1.5	Ω
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2	-	4	V
Dynamic characteristics						
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V ,f=1.0MHz	-	2.2	-	Ω
Forward Transconductance	g _{fs}	V _{DS} =10V, I _D =3A	-	6	-	S
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V f=1.0MHz	-	1200	-	pF
Output Capacitance	C _{oss}		-	80	-	pF
Reverse Transfer Capacitance	C _{rss}		-	1.9	-	pF
Resistive Switching Characteristics						
Turn-on Delay Time	t _{d(ON)}	I _D =8A, V _{DS} =325V R _G =25Ω ,V _{GS} =10V	-	11	-	ns
Rise Time	t _r		-	20.5	-	ns
Turn-off Delay Time	t _{d(OFF)}		-	80	-	ns
Fall Time	t _f		-	32.3	-	ns
Total Gate Charge	Q _g	I _D =8A, V _{DS} =325V V _{GS} =10V	-	24.5	-	nC
Gate to Source Charge	Q _{gs}		-	5.8	-	nC
Gate to Drain("Miller") Charge	Q _{gd}		-	6.5	-	nC
Source-Drain Diode Characteristics						
Continuous Source Current(Body Diode)	I _s		-	-	8	A
Maximum Pulsed Current(Body Diode)	I _{SM}		-	-	32	A
Diode Forward Voltage	V _{SD}	I _{SD} =1A, V _{GS} =0V	-	0.72	1.2	V
Reverse Recovery Time	t _{rr}	I _{SD} =8A, T _J =25℃	-	290	-	ns
Reverse Recovery Charge	Q _{rr}	di /dt=100A/μs	-	5920	-	nC

■ TYPICAL CHARACTERISTICS

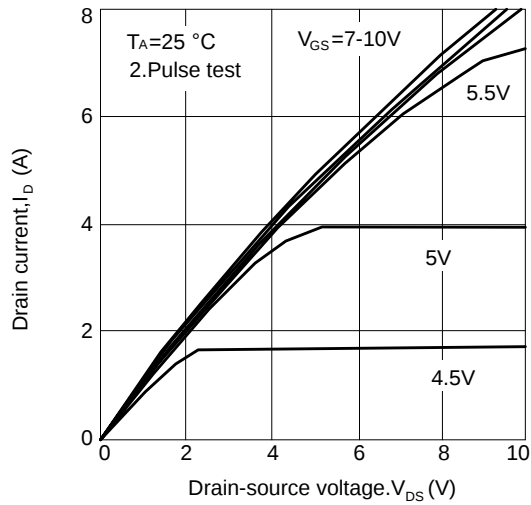


Figure 1: Drain current vs. drain-source voltage

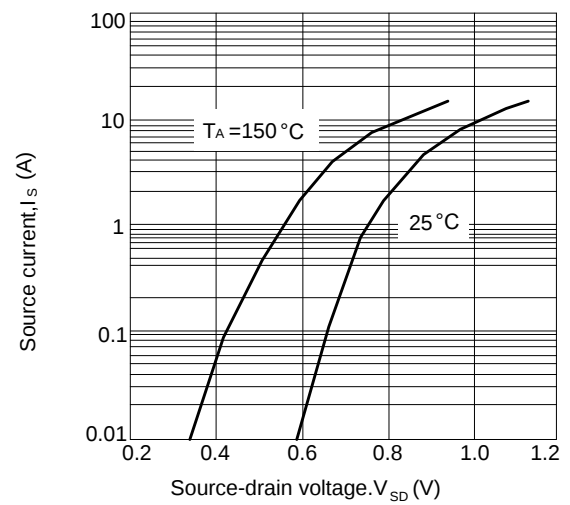


Figure 2: Source current vs. source-drain voltage

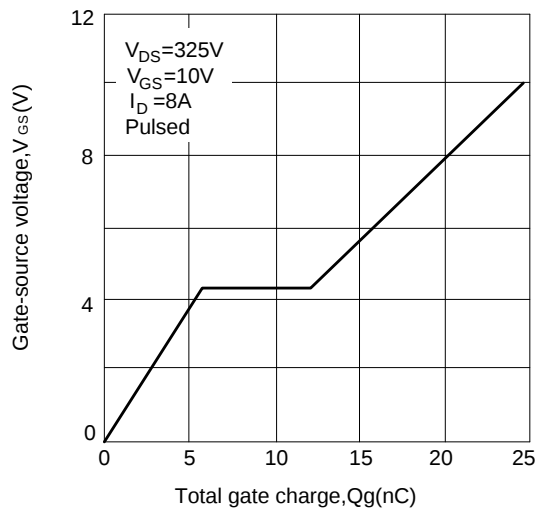


Figure 3: Gate charge characteristics

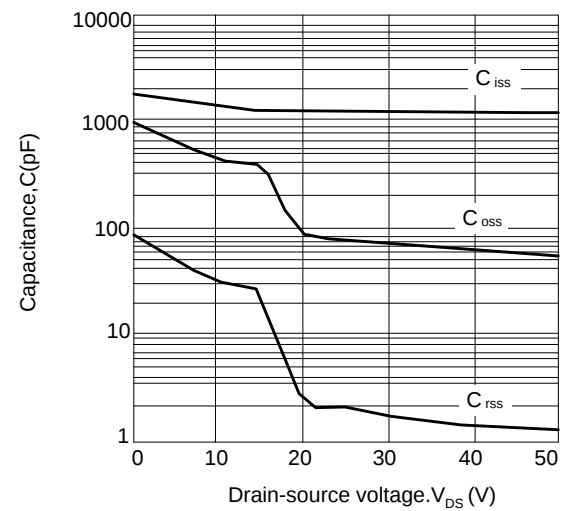


Figure 4: Capacitance characteristics

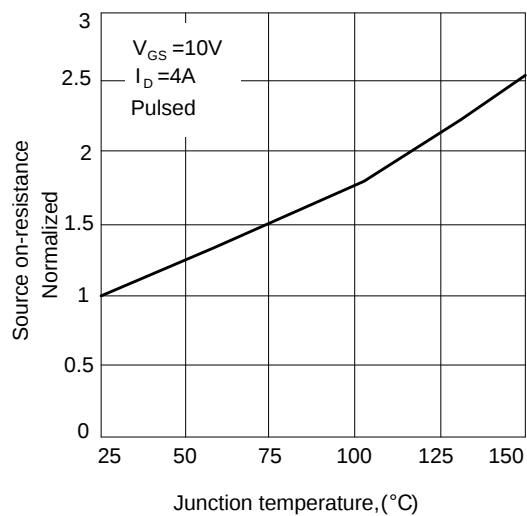


Figure 5: Drain-source on-resistance vs. junction temperature

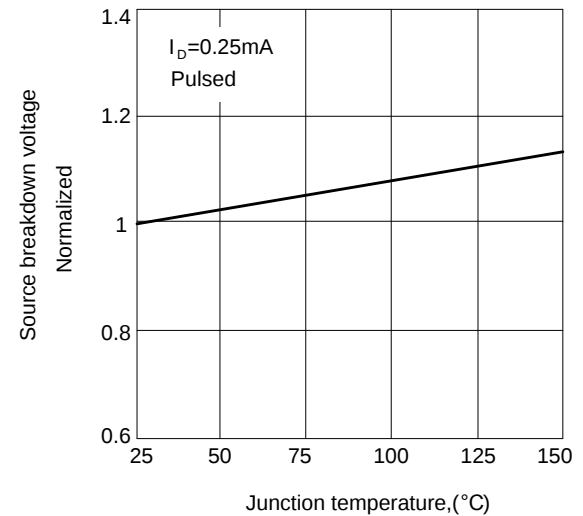


Figure 6: Breakdown voltage vs. junction temperature

■ TYPICAL CHARACTERISTICS(Cont.)

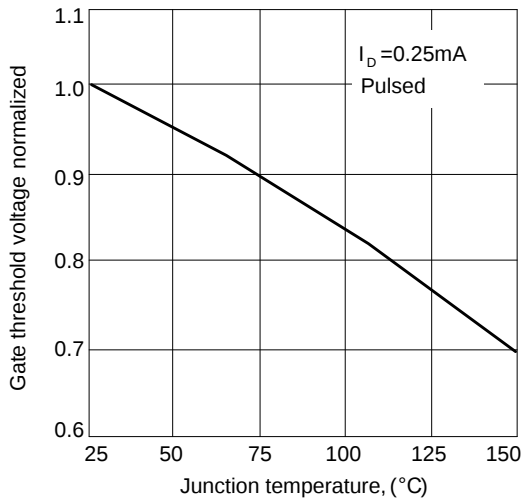


Figure 7: Gate threshold voltage vs. junction temperature

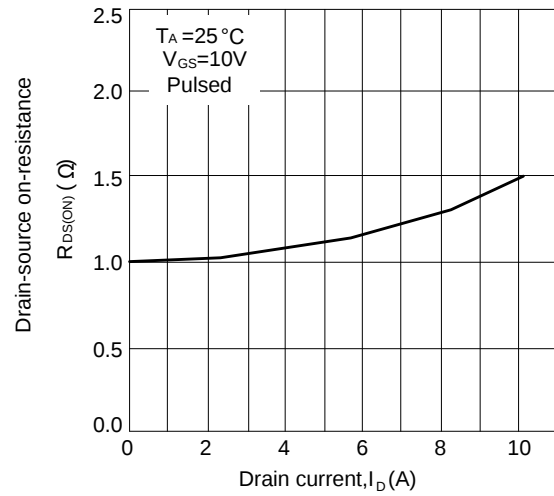


Figure 8: Drain-source on-resistance vs. drain current

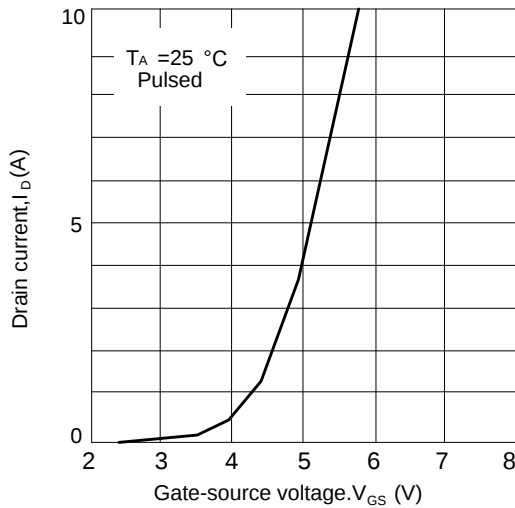


Figure 9: Drain current vs. gate-source voltage

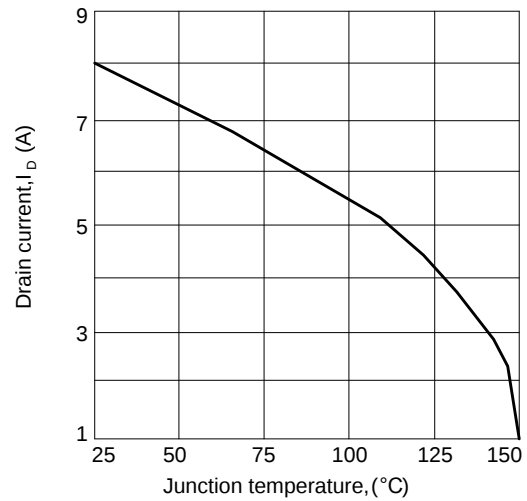


Figure 10: Drain current vs. junction temperature

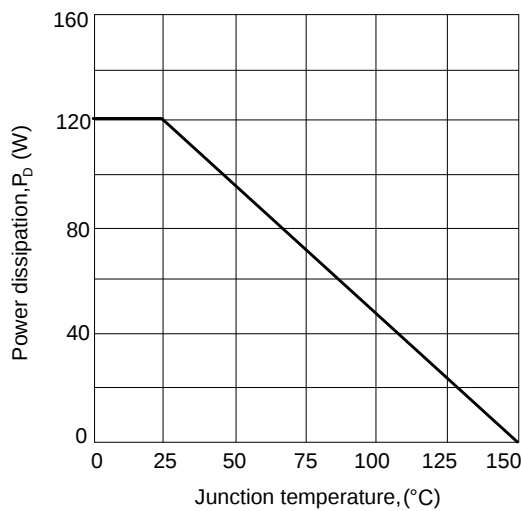


Figure 11: Power dissipation vs. junction temperature

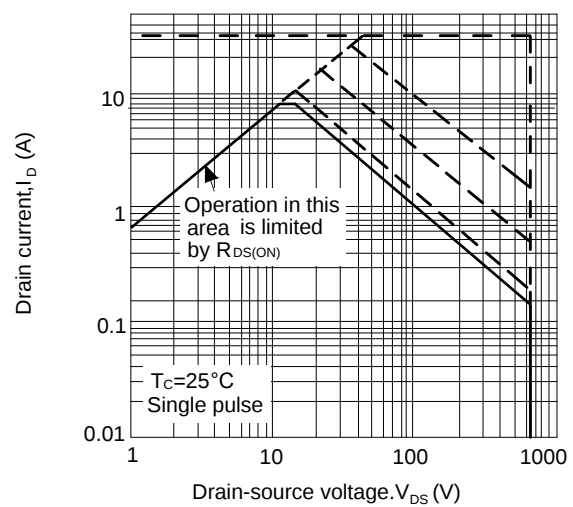


Figure 12: Safe operating area

■ TO-251 PACKAGE OUTLINE DIMENSIONS

